

SuperMOS - SOP8 -40V BV_{DSS}, 13mΩ R_{DS(on)}, -11A I_D P-channel MOSFET

1. Description

The AO4485 is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS(ON)} with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AO4485 is Pb-free.

2. Features

- -40V, R_{DS(ON)}=13 mΩ(Typ), V_{GS}=-10V
R_{DS(ON)}=17mΩ(Typ), V_{GS}=-4.5V
- Fast Switching
- High density cell design for low R_{DS(on)}
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications


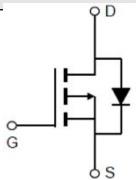
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Quantity per reel	Flammability Rating
AO4485	SOP8	ES4485/LOT	Halogen free	3,000 PCS	UL 94V-0

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	11
		$T_A=75^\circ\text{C}$	8.8
Maximum Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.2
		$T_A=75^\circ\text{C}$	1.9
Pulsed Drain Current ^a	I_{DM}	44	A
Operating Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JA}$	40	°C/W

Note:

a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=-40V$			-1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.6	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-10A$		13	16	m Ω
		$V_{GS}=-4.5V, I_D=-8A$		17	20	
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=-20V,$ $f=1MHz$		2500		pF
Output Capacitance	C_{OSS}			260		
Reverse Transfer Capacitance	C_{RSS}			180		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V, V_{DS}=-20V,$ $I_D=-10A$		42		nC
Gate-to-Source Charge	Q_{GS}			7		
Gate-to-Drain Charge	Q_{GD}			8.8		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V, V_{DS}=-20V,$ $R_L=1\Omega, R_G=3\Omega$		10		ns
Rise Time	t_r			20		
Turn-Off Delay Time	$t_{d(OFF)}$			55		
Fall Time	t_f			30		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=-10A$			-1.2	V

7. Typical Characteristic

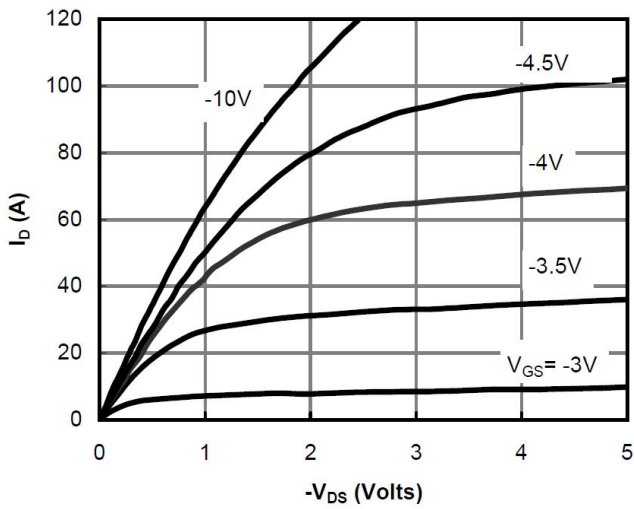


Figure 1: On-Region Characteristics

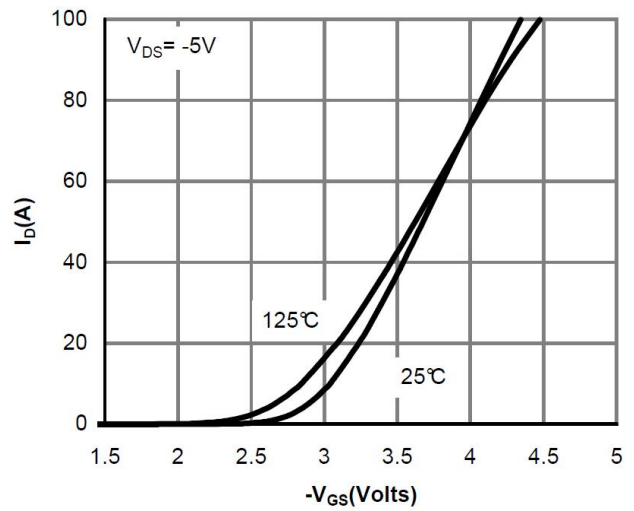


Figure 2: Transfer Characteristics

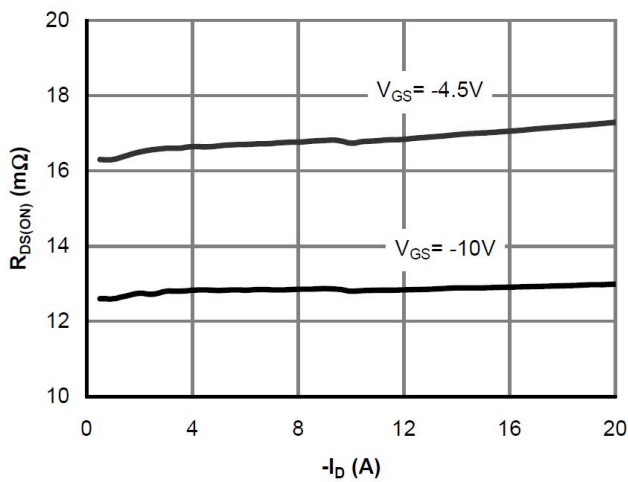


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

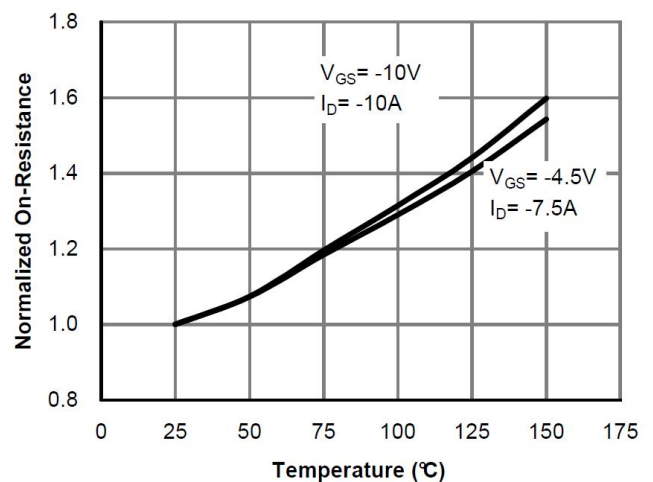


Figure 4: On-Resistance vs. Junction Temperature

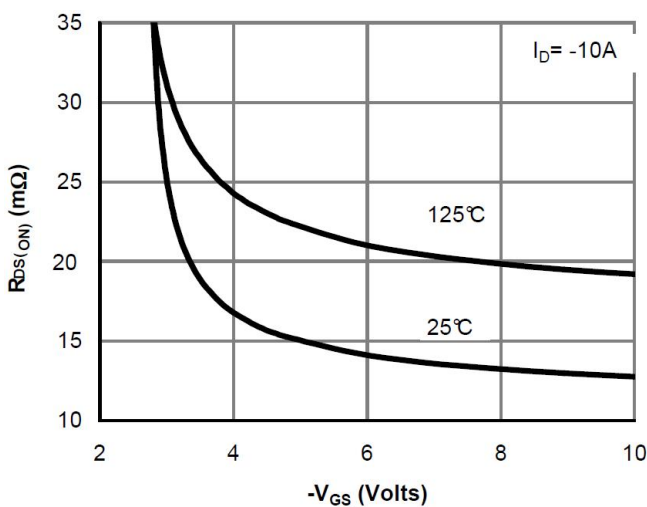


Figure 5: On-Resistance vs. Gate-Source Voltage

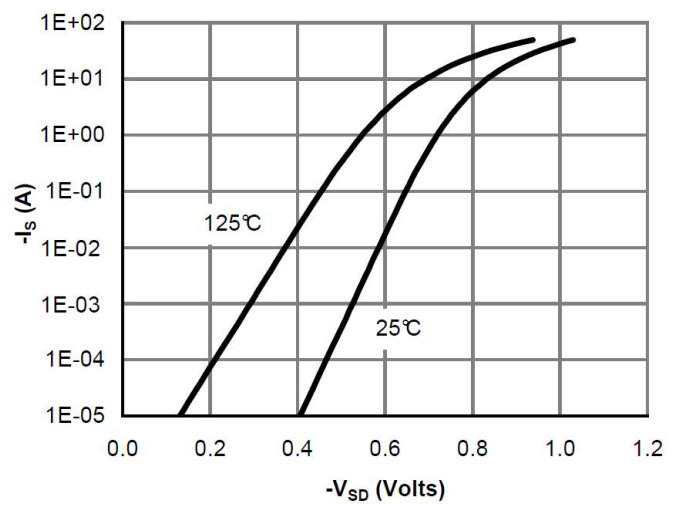


Figure 6: Body-Diode Characteristics

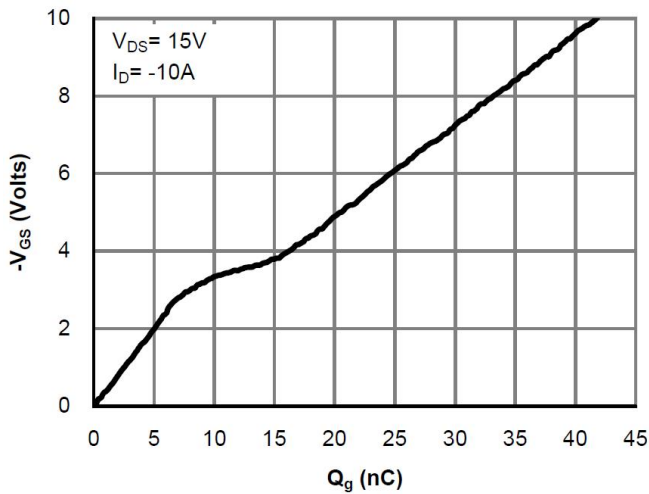


Figure 7: Gate-Charge Characteristics

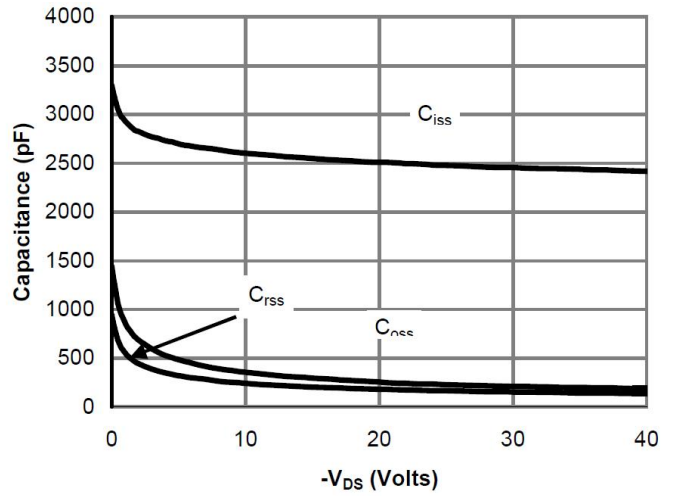


Figure 8: Capacitance Characteristics

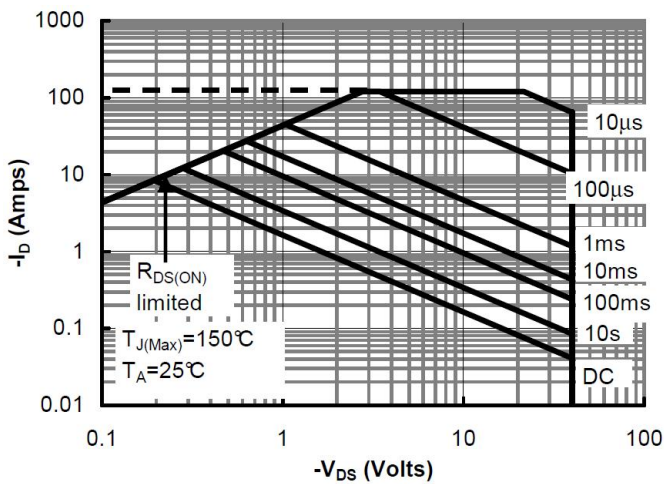


Figure 9: Maximum Forward Biased Safe Operating Area

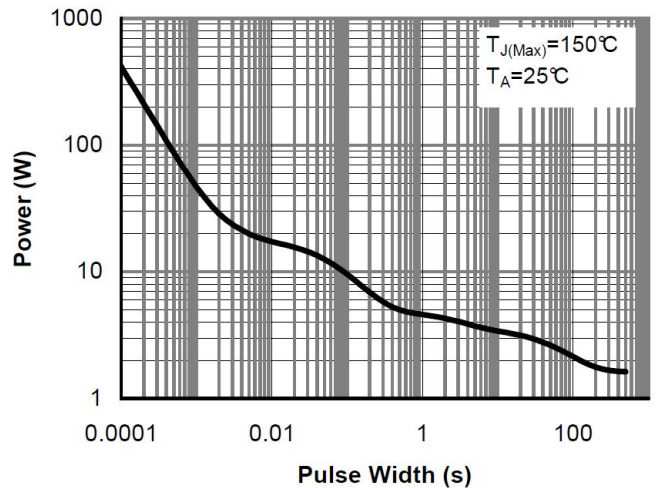


Figure 10: Single Pulse Power Rating Junction-to-Ambient

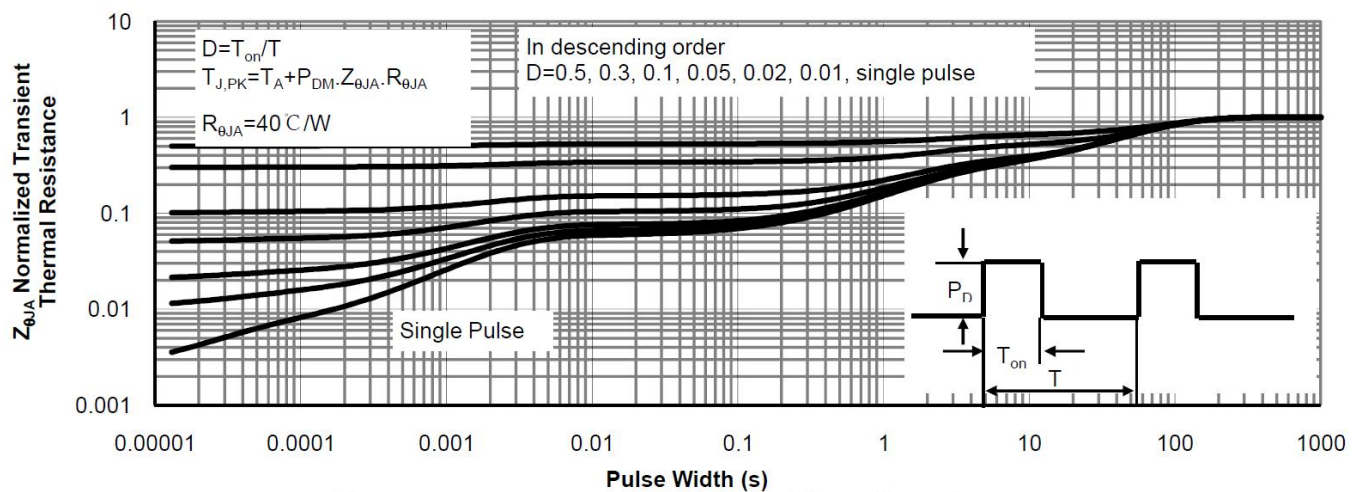
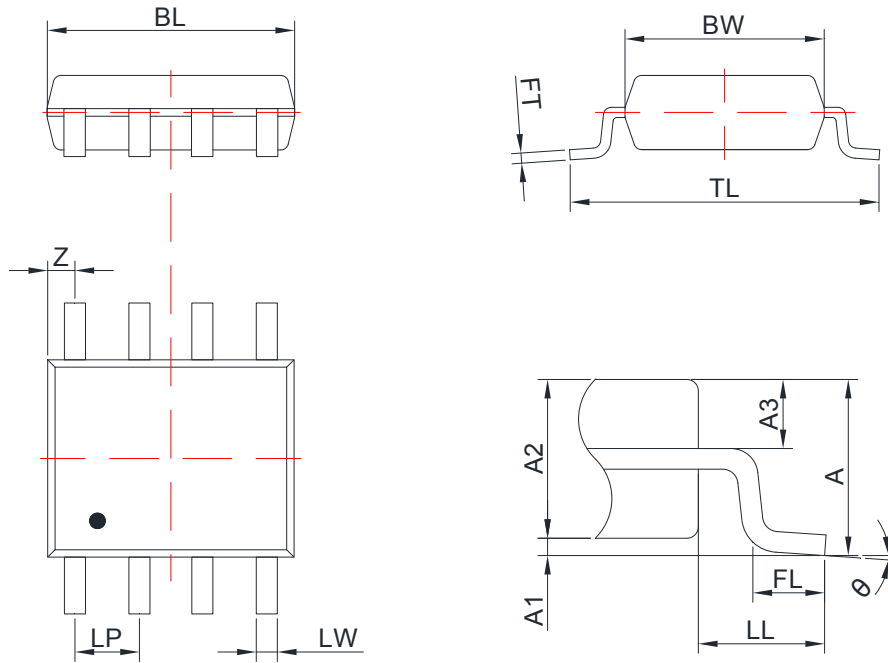


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (SOP8)



COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	1.75		FL	0.50	0.80
A1	0.05	0.15	LP	1.25	1.30
A2	1.40	1.50	LL	1.1 BSC	
A3	0.623 BSC		LW	0.38	0.43
BL	4.92	5.80	TL	5.90	6.10
BW	3.70	4.10	Z	0.54	
FT	0.20	0.21	theta	0°	8°

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